L	Hits	Search Text	DB	Time stamp
Number 5	1105	((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or	USPAT; US-PGPUB;	2004/02/13 12:47
6	452	gallium or Ga or Al) same (implant or implanting or implantation or dope or doped or doping or dopant) (((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or	EPO; JPO; DERWENT; IBM_TDB USPAT	2004/02/13 12:48
7	443	doped or doping or dopant)) and (selective or selectivity) ((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or	USPAT	2004/02/13 12:49
8	196	<pre>doped or doping or dopant)) and (selective or selectivity)) and @ay<=2001 (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or gallium or Ga or Al) same (implant or implanting or implantation or dope or</pre>	USPAT	2004/02/13 12:49
9	160	doped or doping or dopant)) and (selective or selectivity)) and (any<=2001) and (anneal or annealing) ((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/13 12:50
10	685	<pre>doped or doping or dopant) ((((((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity) same (implant or implanting or</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/13 12:51
		implantation or dope or doped or doping or dopant))) not (((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or implanting or implantation or dope or doped or doping or dopant)) and (etch or etching)) and ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (etch or etching)) and ((implant or implanting or implantation or dope or doped or doping or dopant) with (aluminum or al or boron or B! or Ga! or gallium))) and		
11	301	"Si.sub.3 N.sub.4") with (oxide or dioxide or SiO or "SiO?sub.2") with (selective or selectively or selectivity)) and (implant or implanting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/13 12:52
12	3		USPAT;	2004/02/13 13:06 2004/02/13
			US-PGPUB; EPO; JPO; DERWENT; IBM TDB	13:06

14	3	Lawlor-Brian-F.in.	USPAT;	2004/02/13
14	3	Dawlor Briain 1.1	US-PGPUB;	13:06
			EPO; JPO;	
			DERWENT;	
		·	IBM_TDB	2002/12/01
_	1	4514251.pn.	USPAT	2003/12/01
	i		·USPAT	2004/02/13
-	1044	((silicon adj nitride) and SiN or	OSPAI	12:47
		"Si.sub.3 N.sub.4") same (aluminum or		12.17
		gallium or Ga or Al) same (implant or implanting or implantation or dope or		
		doped or doping or dopant)		·
	835	(((silicon adj nitride) and SiN or	USPAT	2003/12/01
-	033	"Si.sub.3 N.sub.4") same (aluminum or		14:47
		gallium or Ga or Al) same (implant or		
		implanting or implantation or dope or		
		doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)		
_	. 779	((((silicon adj nitride) and SiN or	USPAT	2003/12/01
1		"Si.sub.3 N.sub.4") same (aluminum or		14:47
		gallium or Ga or Al) same (implant or		
		implanting or implantation or dope or		
		doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adjoxide) or (silicon adj dioxide) or SiO or		
		SiO?sub.2)		
	546	(((((silicon adj nitride) and SiN or	USPAT	2003/12/01
-	340	"Si.sub.3 N.sub.4") same (aluminum or		13:46
		gallium or Ga or Al) same (implant or		
		implanting or implantation or dope or	1	
		doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adj		
		oxide) or (silicon adj dioxide) or SiO or		
		SiO?sub.2)) and (selective or selectively	,	1
		or selectivity)	USPAT	2003/12/01
	208	(((((silicon adj nitride) and SiN or "Si.sub.3 N.sub.4") same (aluminum or	OSFAI	14:39
		gallium or Ga or Al) same (implant or		
		implanting or implantation or dope or		
		doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adj		
	Ì	oxide) or (silicon adj dioxide) or SiO or		
		SiO?sub.2)) and ((selective or		1
		selectively or selectivity) with (nitride		
		or SiN or "Si.sub.3 N.sub.4"))	USPAT	2004/02/13
-	147		USPAI	12:49
		"Si.sub.3 N.sub.4") with (aluminum or gallium or Ga or Al) with (implant or		12.17
		implanting or implantation or dope or		
1		doped or doping or dopant)		
_	103		USPAT	2003/12/01
		"Si.sub.3 N.sub.4") with (aluminum or		14:47
		gallium or Ga or Al) with (implant or		
		implanting or implantation or dope or		
1		doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)	Habar	2002/12/03
-	94		USPAT	2003/12/01
		"Si.sub.3 N.sub.4") with (aluminum or	1	14.4/
		gallium or Ga or Al) with (implant or implanting or implantation or dope or		
		doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adj		
		oxide) or (silicon adj dioxide) or SiO or		
		Si0?sub.2)		
_	1391		USPAT	2003/12/01
		"Si.sub.3 N.sub.4") same (oxide or		15:27
		dioxide or SiO or "SiO?sub.2") same		
		(selective or selectively or selectivity)	J	

			77.00	2002/12/01
-	1090	(((silicon adj nitride) and SiN or	USPAT	2003/12/01 15:26
		"Si.sub.3 N.sub.4") same (oxide or dioxide or SiO or "SiO?sub.2") same		13.20
		(selective or selectively or		1
		selective of selectively of selectivity)) and (implant or implanting		
	,	or implantation or dope or doped or		
		doping or dopant)		
_	405	((silicon adj nitride) and SiN or	USPAT	2003/12/01
		"Si.sub.3 N.sub.4") same (oxide or		16:40
		dioxide or SiO or "SiO?sub.2") same		
		(selective or selectively or selectivity)		
		same (implant or implanting or		
		implantation or dope or doped or doping		
		or dopant)	***************************************	2002/12/01
-	398	(((silicon adj nitride) and SiN or	USPAT	2003/12/01
		"Si.sub.3 N.sub.4") same (oxide or		15.27
	İ	dioxide or SiO or "SiO?sub.2") same (selective or selectively or selectivity)		
		same (implant or implanting or		
		implantation or dope or doped or doping		
		or dopant)) and @ay<=2001		
_	386	((((silicon adj nitride) and SiN or	USPAT	2003/12/01
		"Si.sub.3 N.sub.4") same (oxide or		15:27
		dioxide or SiO or "SiO?sub.2") same		
		(selective or selectively or selectivity)		
1		same (implant or implanting or		
		implantation or dope or doped or doping		
		or dopant)) and @ay<=2001) not		
		(((((silicon adj nitride) and SiN or		
		"Si.sub.3 N.sub.4") with (aluminum or		
		gallium or Ga or Al) with (implant or		
,		implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001	1	
		and (etch or etching)) and ((silicon adj		
		oxide) or (silicon adj dioxide) or SiO or		
		SiO?sub.2))	†	
	368		USPAT	2003/12/01
		"Si.sub.3 N.sub.4") same (oxide or		15:27
		dioxide or SiO or "SiO?sub.2") same		
		(selective or selectively or selectivity)		
		same (implant or implanting or		
		implantation or dope or doped or doping		
		or dopant)) and @ay<=2001) not	i	
		(((((silicon adj nitride) and SiN or		•
		"Si.sub.3 N.sub.4") with (aluminum or		
		gallium or Ga or Al) with (implant or		
		implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adj		
		oxide) or (silicon adj dioxide) or SiO or		
		SiO?sub.2))) and (etch or etching)		
-	237		USPAT	2003/12/01
		"Si.sub.3 N.sub.4") same (oxide or		15:29
		dioxide or SiO or "SiO?sub.2") same		
		(selective or selectively or selectivity)		
1.		same (implant or implanting or		
		implantation or dope or doped or doping		
		or dopant)) and @ay<=2001) not		
		(((((silicon adj nitride) and SiN or		
		"Si.sub.3 N.sub.4") with (aluminum or		
		gallium or Ga or Al) with (implant or		
		implanting or implantation or dope or doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adj		
	1.	oxide) or (silicon adj dioxide) or SiO or		
		SiO?sub.2))) and (etch or etching)) and		
		((implant or implanting or implantation		
	1	or dope or doped or doping or dopant)		
	1	with (aluminum or al or boron or B! or		
		Ga! or gallium))		

	1.0	5 ((((((silicon adj nitride) and SiN or	USPAT	2003/12/01
_	19	"Si.sub.3 N.sub.4") same (oxide or	001111	16:40
		dioxide or SiO or "SiO?sub.2") same		
		(selective or selectively or selectivity)		
	•	same (implant or implanting or		
		implantation or dope or doped or doping		
		implantation of dope of doped of doping		
		or dopant)) and @ay<=2001) not		
		(((((silicon adj nitride) and SiN or		
	•	"Si.sub.3 N.sub.4") with (aluminum or		
		gallium or Ga or Al) with (implant or	i	
		implanting or implantation or dope or		
		doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adj		
		oxide) or (silicon adj dioxide) or SiO or		
	-	SiO?sub.2))) and (etch or etching)) and		
		((implant or implanting or implantation		
		or dope or doped or doping or dopant)		
		with (aluminum or al or boron or B! or		
		Ga! or gallium))) and @py<=2001	1	
_	13	4 (((((((silicon adj nitride) and SiN or	USPAT	2004/02/13
		"Si.sub.3 N.sub.4") same (oxide or	1	13:06
	ì	dioxide or SiO or "SiO?sub.2") same		
		(selective or selectively or selectivity)		
		same (implant or implanting or		
		implantation or dope or doped or doping		
		or dopant)) and @ay<=2001) not		
		(((((silicon adj nitride) and SiN or		
		"Si.sub.3 N.sub.4") with (aluminum or		
		gallium or Ga or Al) with (implant or		
		implanting or implantation or dope or		
		doped or doping or dopant)) and @ay<=2001		
		and (etch or etching)) and ((silicon adj	·	
		oxide) or (silicon adj dioxide) or SiO or		
		SiO?sub.2))) and (etch or etching)) and		
		((implant or implanting or implantation		
		((implant or implanting or implantation		ļ
		or dope or doped or doping or dopant)		
		with (aluminum or al or boron or B! or	İ	
		Ga! or gallium))) and @py<=2001) and		
		(((silicon adj nitride) and SiN or		
		"Si.sub.3 N.sub.4") with (oxide or		
		dioxide or SiO or "SiO?sub.2"))	HODAM	2002/12/02
_	4	31 ((silicon adj nitride) and SiN or	USPAT	2003/12/02
		"Si.sub.3 N.sub.4") with (oxide or	1	15:52
		dioxide or SiO or "SiO?sub.2") with		
		(selective or selectively or selectivity)		0000/10/00
-	3)7 (((silicon adj nitride) and SiN or	USPAT	2003/12/02
		"Si.sub.3 N.sub.4") with (oxide or		10:01
		dioxide or SiO or "SiO?sub.2") with		
		(selective or selectively or		
		selectivity)) and (implant or implanting		1
		or implantation or dope or doped or		
		doping or dopant)		
_	2	32 ((((silicon adj nitride) and SiN or	USPAT	2004/02/13
	-	"Si.sub.3 N.sub.4") with (oxide or		12:52
	1	dioxide or SiO or "SiO?sub.2") with		
		(selective or selectively or		
}		selectivity)) and (implant or implanting		
1		or implantation or dope or doped or		
		TOT THISTAILCHOLDING OF MODES OF MODES OF	4	i i
		doping or dopant)) and (etch or etching)		

	167	(((((silicon adj nitride) and SiN or	USPAT	2003/12/02
-	107	"Si.sub.3 N.sub.4") with (oxide or		15:36
		dioxide or SiO or "SiO?sub.2") with		
		(selective or selectively or		
		selectivity)) and (implant or implanting		·
		or implantation or dope or doped or		-
		doping or dopant)) and (etch or etching)		
	ļ	and @ay<=2001) and ((implant or		
		implanting or implantation or dope or		
		doped or doping or dopant) with (al! or		
		aluminum or Ga or gallium or boron or		
	[B!)) ("3886569" "4806199" "4807016"	USPAT	2003/12/02
-	21	"5275972" "5286344" "5300463"	001111	12:08
		"542457.0" "5468342" "5562801"	·	
		"5626716" "5695658" "5759888"		
		"5814563" "5817580" "5841195"		
		"5843845" "5843847" "5855962"		
		"5965035" "6051870" "6239017").PN.		
_	290	438/705.ccls.	USPAT	2003/12/02
				15:36
_	650	438/706.ccls.	USPAT	2003/12/02
			***************************************	15:36 2003/12/02
_	118.	348/714.ccls.	USPAT	15:36
		100/500	USPAT	2003/12/02
-	729	438/723.ccls.	USPAI	15:36
	202	420 /724	USPAT	2003/12/02
-	393	438/724.ccls.	331111	15:37
	38	((silicon adj nitride) and SiN or	US-PGPUB;	2004/02/13
_	30	"Si.sub.3 N.sub.4") with (oxide or	EPO; JPO;	12:51
		dioxide or SiO or "SiO?sub.2") with	DERWENT	
•		(selective or selectively or selectivity)		